

Product data sheet

### 1. General description

AC Thyristor power switch in a SOT54 (TO-92) plastic package with self-protective capabilities against low and high energy transients.

### 2. Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- Remote gate separates the gate driver from the effects of the load current
- · Safe clamping of low energy over-voltage transients
- High voltage capability
- Self-protective turn-on during high energy voltage transients
- Very high noise immunity

### 3. Applications

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- Fan motor circuits
- Pump motor circuits
- Lower-power highly inductive, resistive and safety loads

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	13	A
Tj	junction temperature		-	-	125	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 75 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	0.8	A
V <sub>PP</sub>	peak pulse voltage	$T_j$ = 25 °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; Fig. 6	-	-	2.5	kV





### AC Thyristor power switch

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	1	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	1	-	10	mA
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
Dynamic cl	haracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_{D} = 400 \text{ V};  \text{T}_{\text{j}} = 125 ^{\circ}\text{C};$ $I_{\text{T}(\text{RMS})} = 0.8 \text{ A};  \text{d}\text{V}_{\text{com}}/\text{d}\text{t} = 20  \text{V}/\mu\text{s};$ (snubberless condition); gate open circuit; Fig. 14; Fig. 15	0.5	-	-	A/ms

# 5. Pinning information

Table 2	. Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	СМ	common		LD
2	G	gate		
3	LD	load		G —●[ CM 001aaj924
			TO-92 (SOT54)	

## 6. Ordering information

Table 3. Ordering inf	ormation		
Type number	Package		
	Name	Description	Version
ACT108-800E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

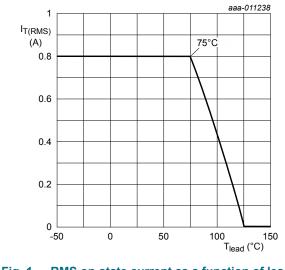
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### 7. Limiting values

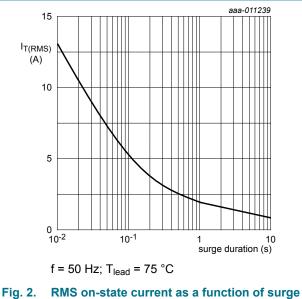
#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 75 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	13	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	14.3	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$t_p$ = 10 ms; sine-wave pulse	-	0.84	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/µs	-	100	A/µs
I <sub>GM</sub>	peak gate current	t = 20 μs	-	1	А
V <sub>GM</sub>	peak gate voltage	positive applied gate voltage	-	15	V
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
V <sub>PP</sub>	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses; Fig. 6	-	2.5	kV

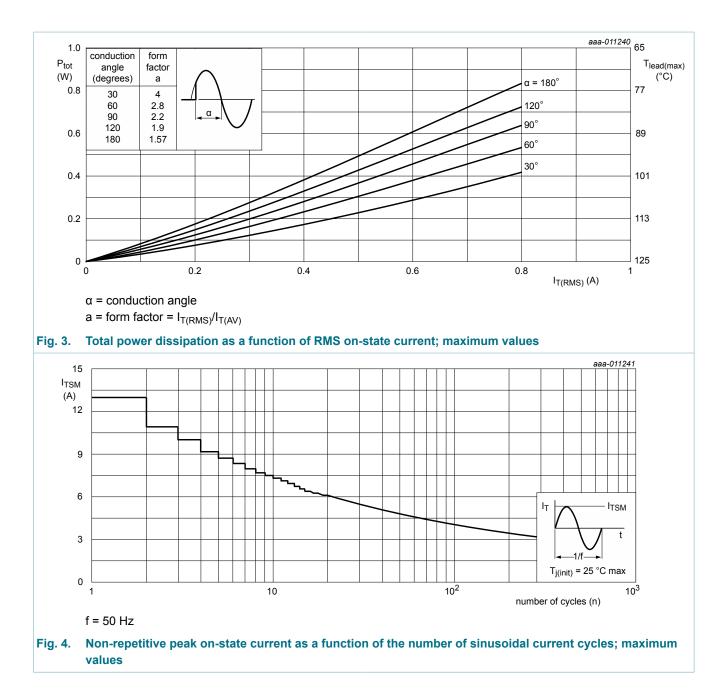






duration; maximum values

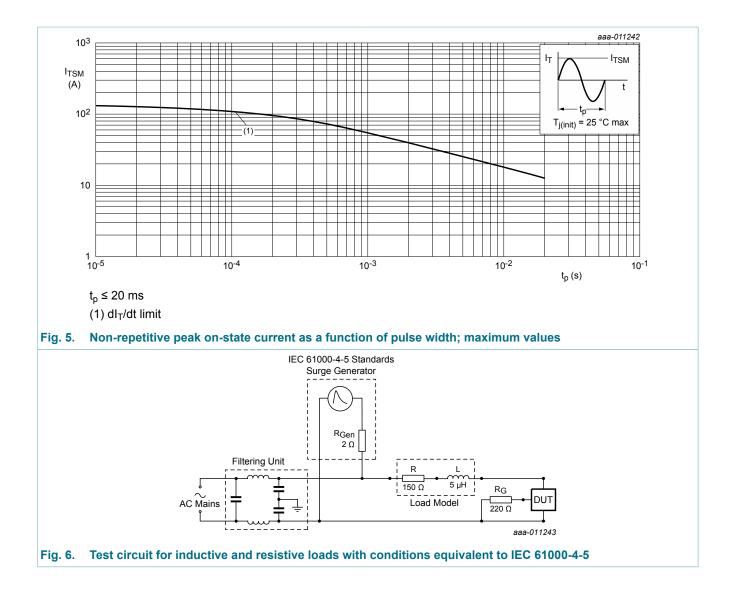
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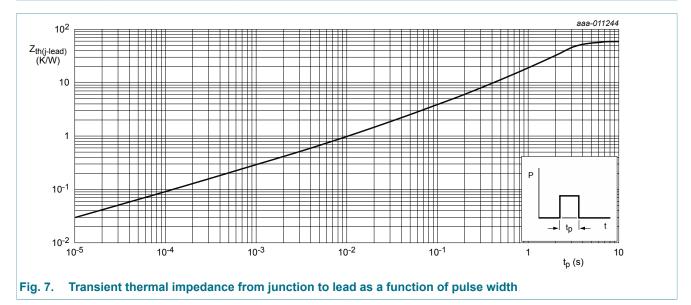
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### 8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	full cycle with heatsink compound; Fig. 7	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm	-	150	-	K/W



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### 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static char	acteristics		·			
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; Fig. 8	1	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 100 \text{ mA}; \text{ LD- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	1	-	10	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	25	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	20	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	1.3	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 25 °C; Fig. 12	-	-	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 125 °C; Fig. 12	0.15	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.2	mA
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
Dynamic cl	naracteristics	· · · · · · · · · · · · · · · · · · ·	I			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; T <sub>j</sub> = 125 °C; $I_{T(RMS)}$ = 0.8 A; $dV_{com}/dt$ = 20 V/µs; (snubberless condition); gate open circuit; Fig. 14; Fig. 15	0.5	-	-	A/ms

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#### AC Thyristor power switch

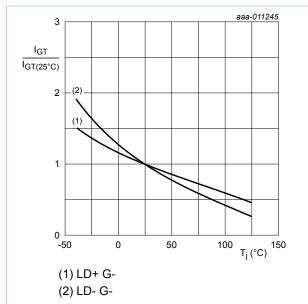


Fig. 8. Normalized gate trigger current as a function of junction temperature

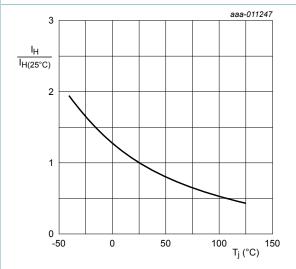
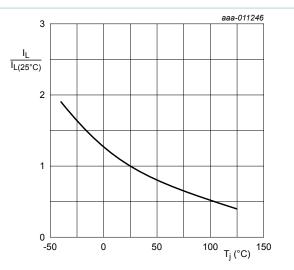
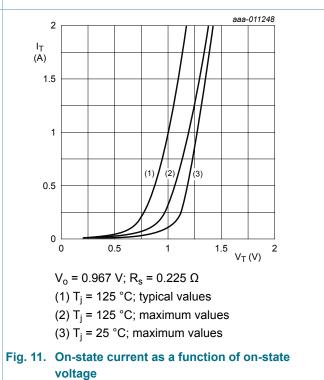


Fig. 10. Normalized holding current as a function of junction temperature





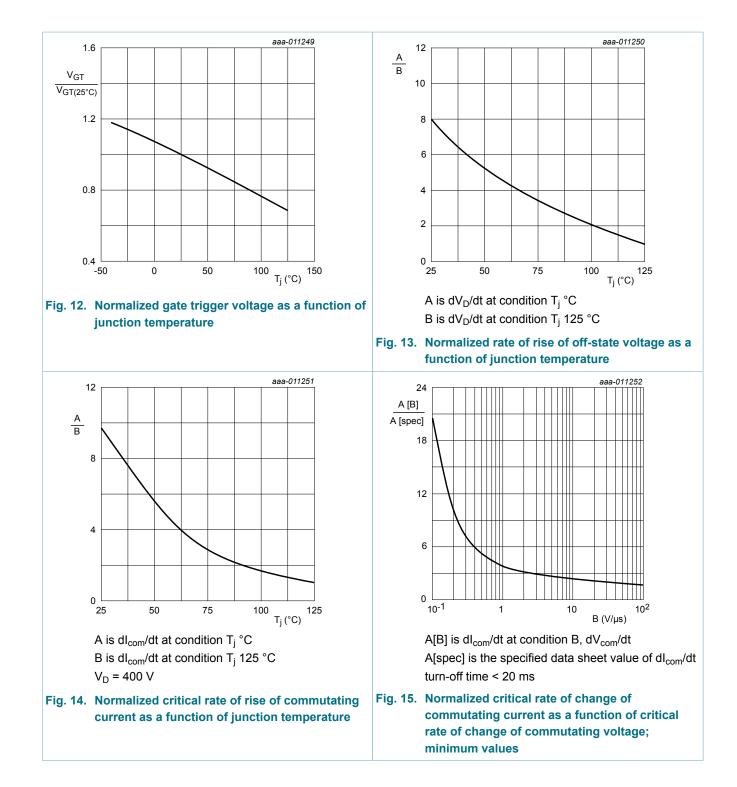


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### **10. Package outline**

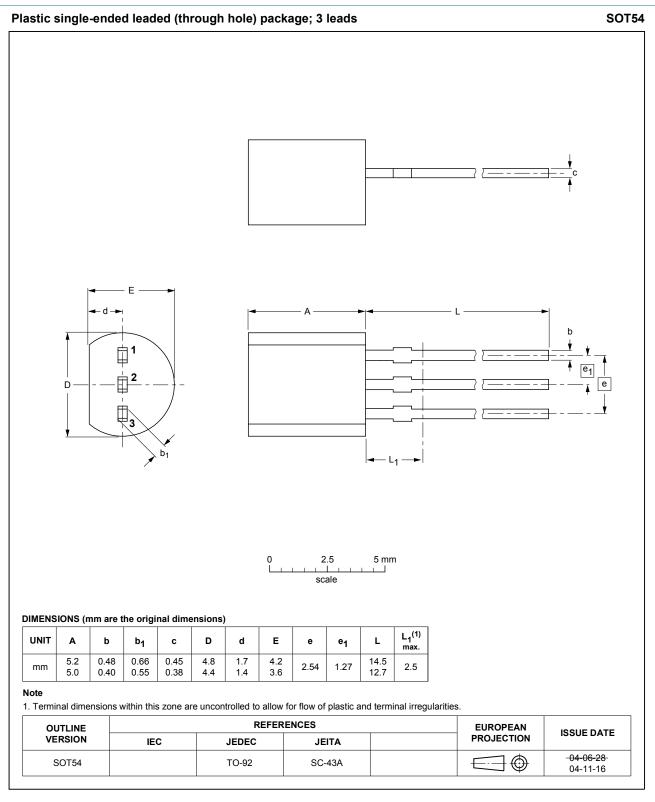


 Fig. 16. Package outline TO-92 (SOT54)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### AC Thyristor power switch

### **12. Contents**

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	6
9	Characteristics	7
10	Package outline	10
11		
11	Legal information	11
11 11.1	Legal information Data sheet status	
••	-	11
11.1	Data sheet status	11 11

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